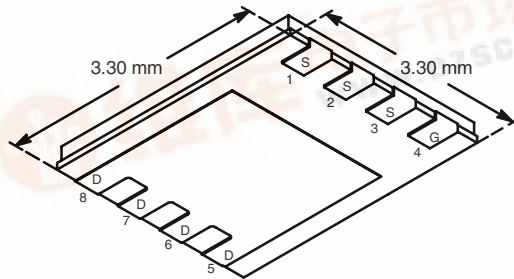


N-Channel 40-V (D-S) MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A) ^a	Q _g (Typ.)
40	0.0076 at V _{GS} = 10 V	35	12.5 nC
	0.0092 at V _{GS} = 4.5 V	35	

PowerPAK® 1212-8



Bottom View

Ordering Information: SiS434DN-T1-GE3 (Lead (Pb)-free and Halogen-free)

FEATURES

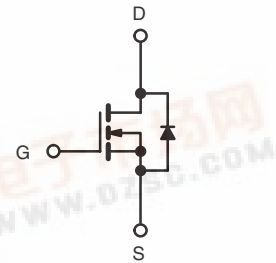
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- 100 % R_g Tested
- 100 % UIS Tested
- Compliant to RoHS Directive 2002/95/EC



RoHS
 COMPLIANT
 HALOGEN
 FREE

APPLICATIONS

- POL



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T_A = 25 °C, unless otherwise noted

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	40	V
Gate-Source Voltage	V _{GS}	± 20	
Continuous Drain Current (T _J = 150 °C)	I _D	T _C = 25 °C	35 ^a
		T _C = 70 °C	35 ^a
		T _A = 25 °C	17.6 ^{b, c}
		T _A = 70 °C	14.1 ^{b, c}
Pulsed Drain Current	I _{DM}	60	A
Avalanche Current	I _{AS}	30	
Avalanche Energy	E _{AS}	45	mJ
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C	35 ^a
		T _A = 25 °C	3.2 ^{b, c}
Maximum Power Dissipation	P _D	T _C = 25 °C	52
		T _C = 70 °C	33
		T _A = 25 °C	3.8 ^{b, c}
		T _A = 70 °C	2 ^{b, c}
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150	°C
Soldering Recommendations (Peak Temperature) ^{d, e}		260	

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{b, f}	R _{thJA}	24	33	°C/W
Maximum Junction-to-Case (Drain)	R _{thJC}	1.9	2.4	

Notes:

- Package Limited.
- Surface Mounted on 1" x 1" FR4 board.
- t = 10 s.
- See Solder Profile (www.vishay.com/ppg?773257). The PowerPAK 1212 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.
- Maximum under Steady State conditions is 81 °C/W.



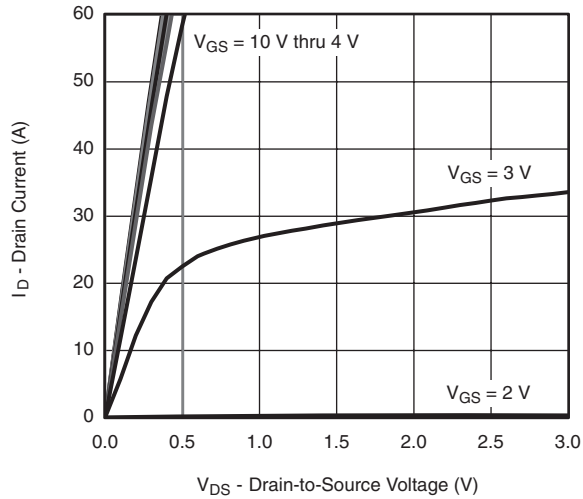
SPECIFICATIONS $T_J = 25^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	40			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\ \mu\text{A}$		46		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			- 5		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	1.2		2.2	V
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 40\text{ V}, V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 40\text{ V}, V_{GS} = 0\text{ V}, T_J = 55^\circ\text{C}$			5	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	40			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 16.2\text{ A}$		0.0063	0.0076	Ω
		$V_{GS} = 4.5\text{ V}, I_D = 14.7\text{ A}$		0.0077	0.0092	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 16.2\text{ A}$		60		S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		1530		pF
Output Capacitance	C_{oss}			240		
Reverse Transfer Capacitance	C_{rss}			100		
Total Gate Charge	Q_g	$V_{DS} = 20\text{ V}, V_{GS} = 10\text{ V}, I_D = 16.2\text{ A}$		25	40	nC
		$V_{DS} = 20\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 16.2\text{ A}$		12.5	19	
Gate-Source Charge	Q_{gs}	$V_{DS} = 20\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 16.2\text{ A}$		3.9		
Gate-Drain Charge	Q_{gd}			3.9		
Gate Resistance	R_g	$f = 1\text{ MHz}$	0.2	1.3	2.6	Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 20\text{ V}, R_L = 2\ \Omega$ $I_D \cong 10\text{ A}, V_{GEN} = 4.5\text{ V}, R_g = 1\ \Omega$		20	30	ns
Rise Time	t_r			15	25	
Turn-Off Delay Time	$t_{d(off)}$			25	40	
Fall Time	t_f			12	20	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 20\text{ V}, R_L = 2\ \Omega$ $I_D \cong 10\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\ \Omega$		10	15	
Rise Time	t_r			10	15	
Turn-Off Delay Time	$t_{d(off)}$			25	40	
Fall Time	t_f			7	15	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_C = 25^\circ\text{C}$			43	A
Pulse Diode Forward Current ^a	I_{SM}				35	
Body Diode Voltage	V_{SD}	$I_S = 10\text{ A}, V_{GS} = 0\text{ V}$		0.8	1.2	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = 10\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25^\circ\text{C}$		30	45	ns
Body Diode Reverse Recovery Charge	Q_{rr}			33	50	nC
Reverse Recovery Fall Time	t_a			20		ns
Reverse Recovery Rise Time	t_b			10		

Notes:

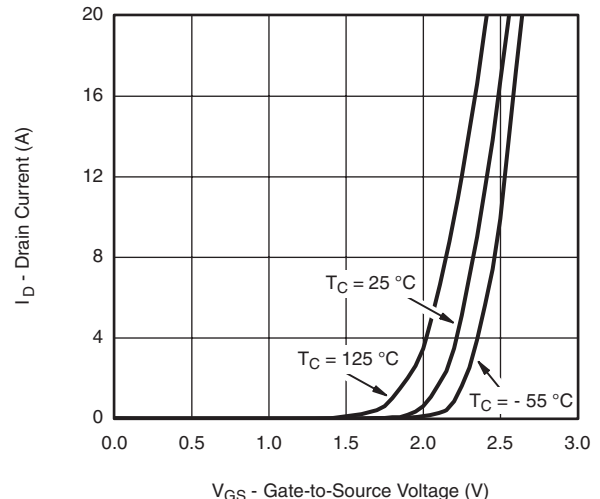
- a. Pulse test; pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

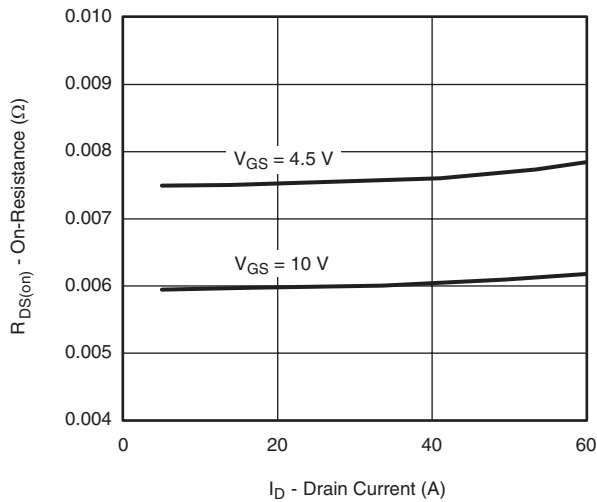
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



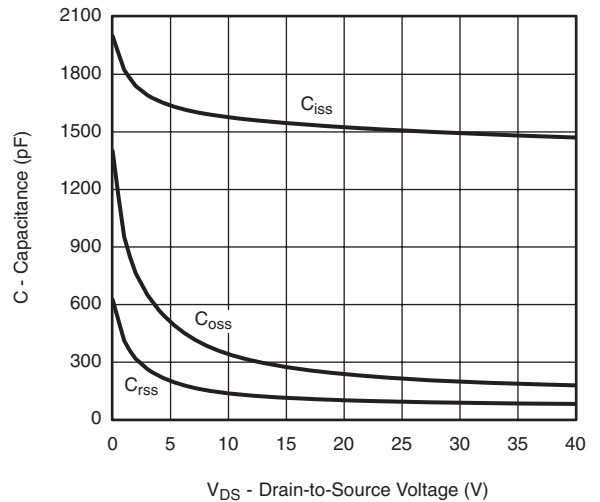
Output Characteristics



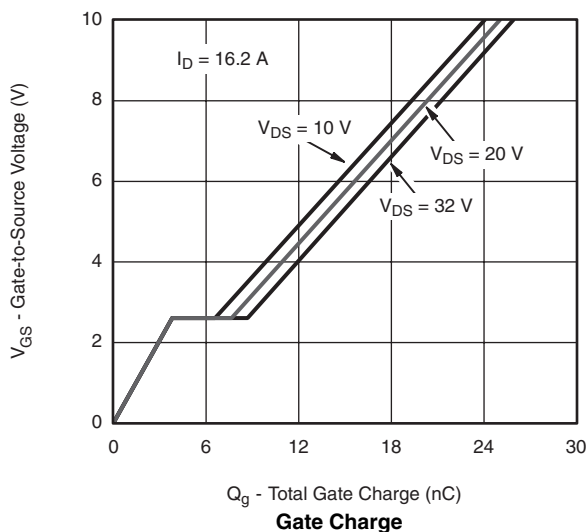
Transfer Characteristics



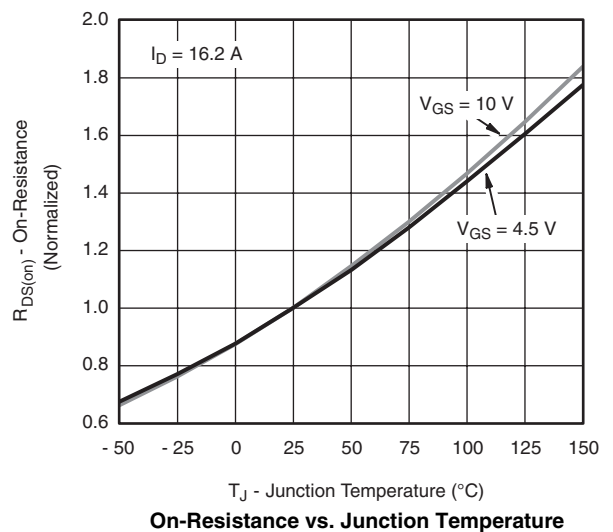
On-Resistance vs. Drain Current and Gate Voltage



Capacitance

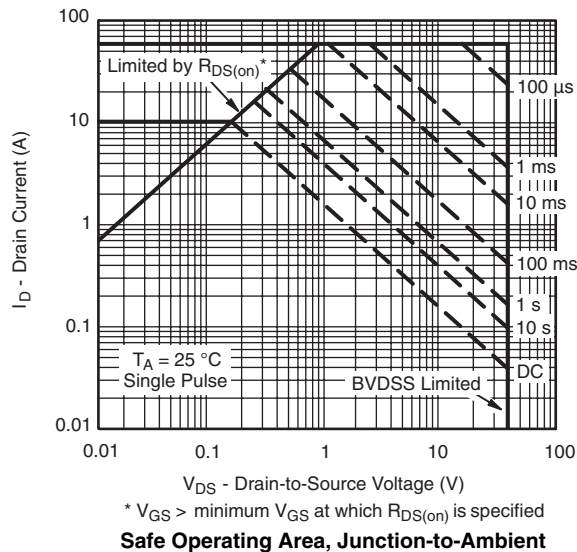
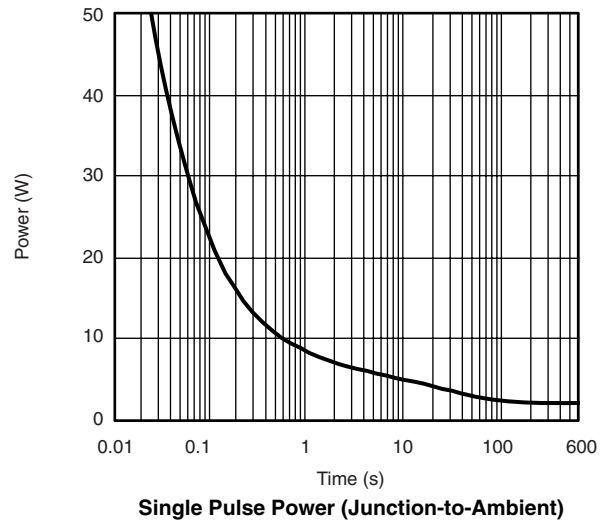
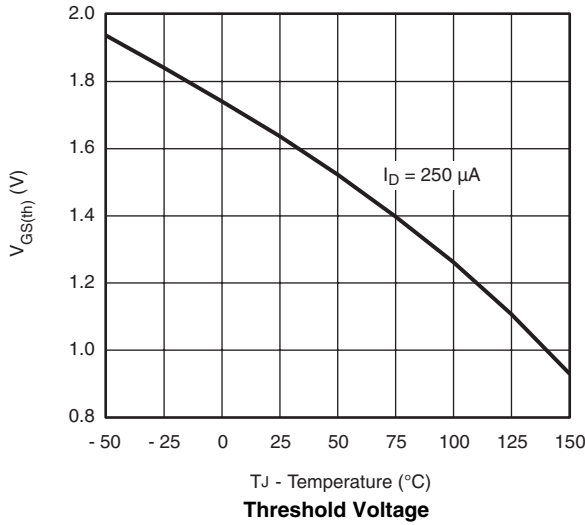
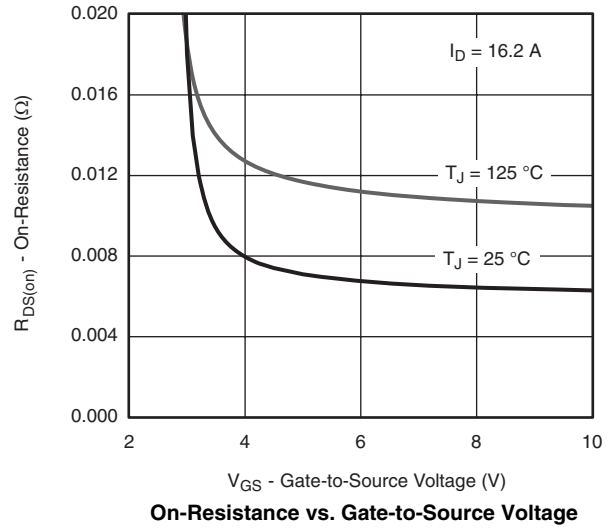
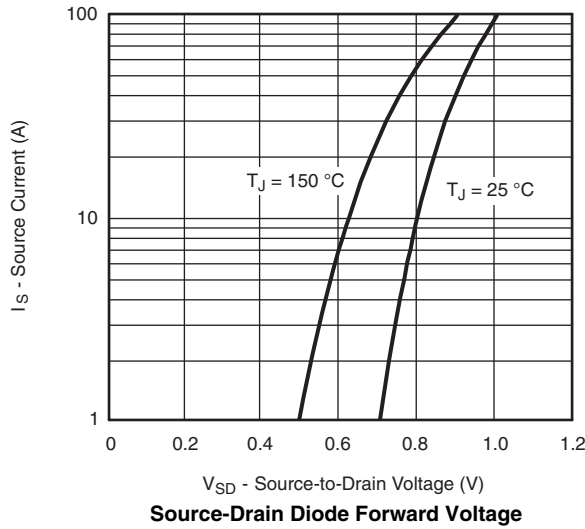


Gate Charge

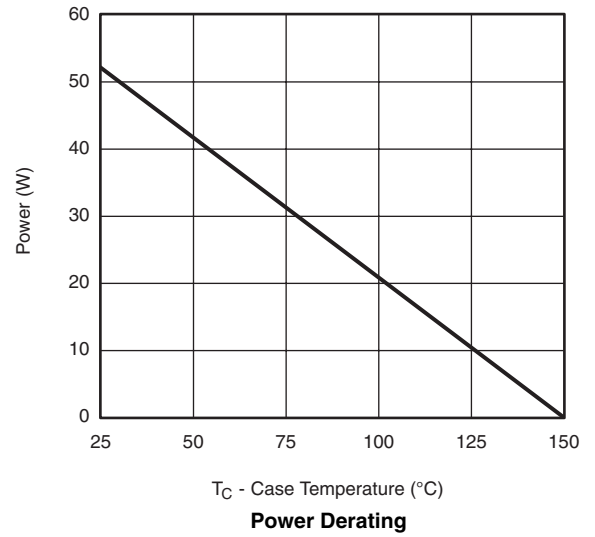
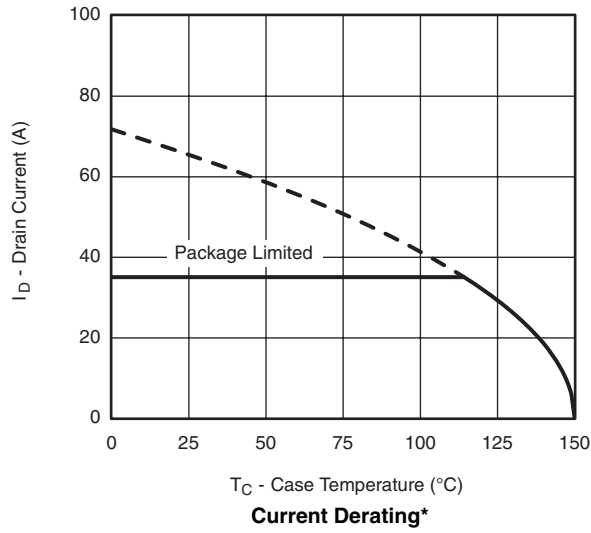


On-Resistance vs. Junction Temperature

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

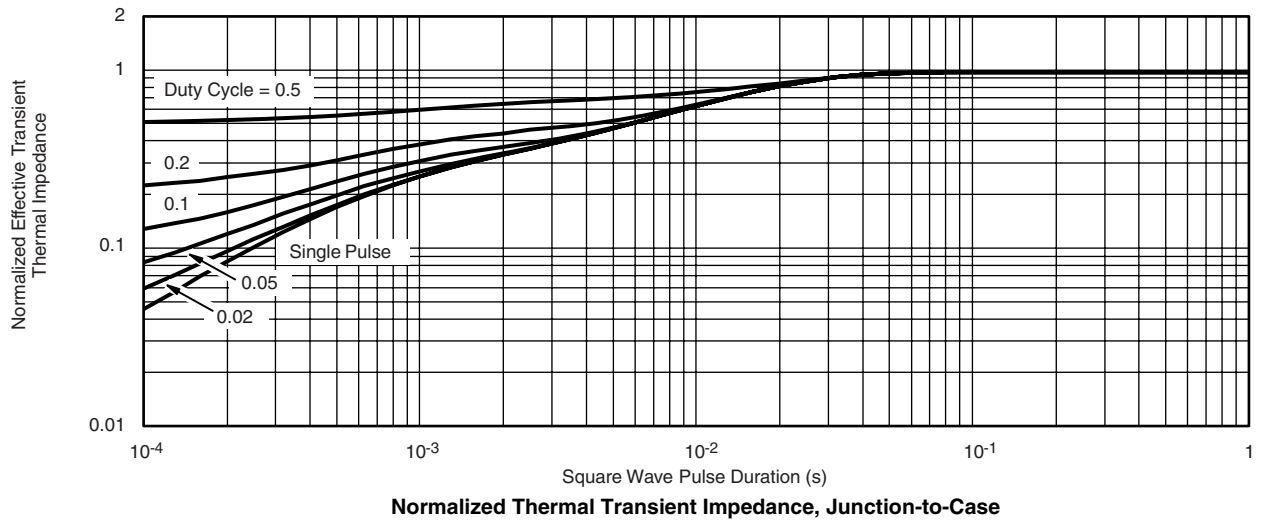
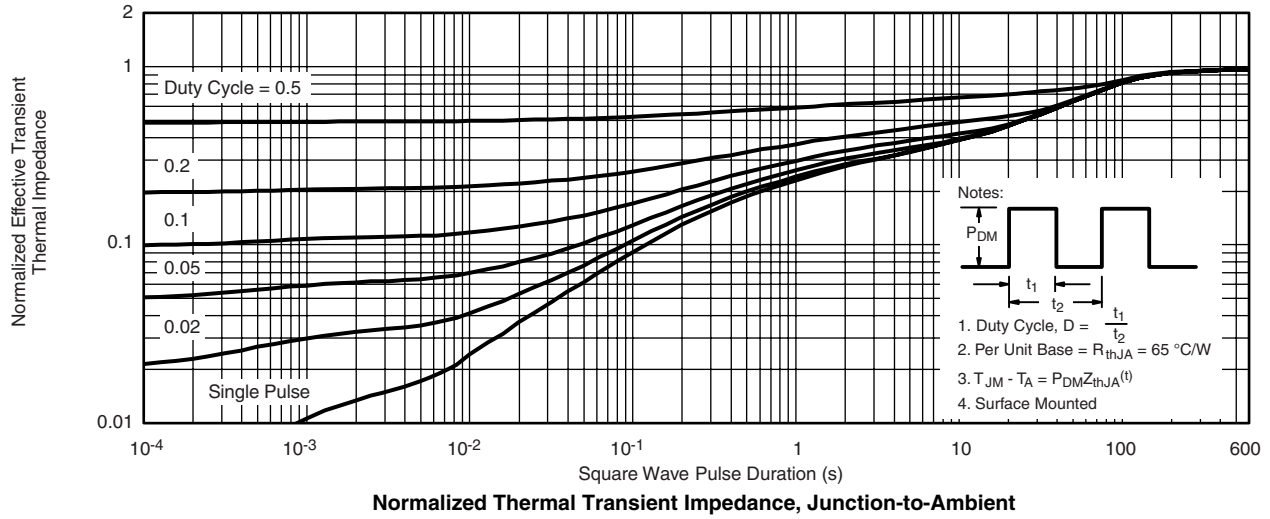


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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